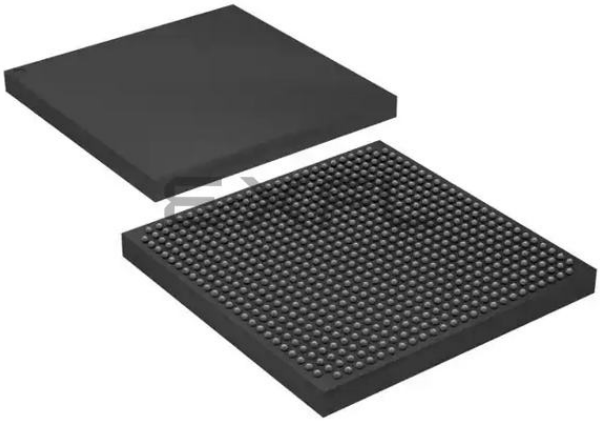

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	2432
Number of Logic Elements/Cells	24320
Total RAM Bits	311296
Number of I/O	508
Number of Gates	1537000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k600cf672c8n

…and More Features

- Low-power operation design
  - 1.8-V supply voltage (see Table 2)
  - Copper interconnect reduces power consumption
  - MultiVolt™ I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
  - ESBs offering programmable power-saving mode
- Flexible clock management circuitry with up to four phase-locked loops (PLLs)
  - Built-in low-skew clock tree
  - Up to eight global clock signals
  - ClockLock™ feature reducing clock delay and skew
  - ClockBoost™ feature providing clock multiplication and division
  - ClockShift™ feature providing programmable clock phase and delay shifting
- Powerful I/O features
  - Compliant with peripheral component interconnect Special Interest Group (PCI SIG) ***PCI Local Bus Specification, Revision 2.2*** for 3.3-V operation at 33 or 66 MHz and 32 or 64 bits
  - Support for high-speed external memories, including DDR synchronous dynamic RAM (SDRAM) and ZBT static RAM (SRAM)
  - 16 input and 16 output LVDS channels at 840 megabits per second (Mbps)
  - Direct connection from I/O pins to local interconnect providing fast t_{CO} and t_{SU} times for complex logic
  - MultiVolt I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
  - Programmable clamp to V_{CCIO}
  - Individual tri-state output enable control for each pin
  - Programmable output slew-rate control to reduce switching noise
  - Support for advanced I/O standards, including low-voltage differential signaling (LVDS), LVPECL, PCI-X, AGP, CTT, SSTL-3 and SSTL-2, GTL+, and HSTL Class I
  - Supports hot-socketing operation
  - Pull-up on I/O pins before and during configuration

Table 2. APEX 20KC Supply Voltages

Feature	Voltage
Internal supply voltage (V_{CCINT})	1.8 V
MultiVolt I/O interface voltage levels (V_{CCIO})	1.8 V, 2.5 V, 3.3 V, 5.0 V *(1)*

Note to Table 2:
(1) APEX 20KC devices can be 5.0-V tolerant by using an external resistor.

Table 4. APEX 20KC FineLine BGA Package Options & I/O Count Notes (1), (2)			
Device	**484 Pin**	**672 Pin**	**1,020 Pin**
EP20K200C	376		
EP20K400C		488 (3)	
EP20K600C		508 (3)	588
EP20K1000C		508 (3)	708

Notes to Tables 3 and 4:

(1) I/O counts include dedicated input and clock pins.

(2) APEX 20KC device package types include plastic quad flat pack (PQFP), 1.27-mm pitch ball-grid array (BGA), and 1.00-mm pitch FineLine BGA™ packages.

(3) This device uses a thermally enhanced package, which is taller than the regular package. Consult the *Altera Device Package Information Data Sheet* for detailed package size information.

Table 5. APEX 20KC QFP & BGA Package Sizes				
Feature	**208-Pin PQFP**	**240-Pin PQFP**	**356-Pin BGA**	**652-Pin BGA**
Pitch (mm)	0.50	0.50	1.27	1.27
Area (mm^2)	924	1,218	1,225	2,025
Length × Width (mm × mm)	30.4 × 30.4	34.9 × 34.9	35.0 × 35.0	45.0 × 45.0

Table 6. APEX 20KC FineLine BGA Package Sizes			
Feature	**484 Pin**	**672 Pin**	**1,020 Pin**
Pitch (mm)	1.00	1.00	1.00
Area (mm^2)	529	729	1,089
Length × Width (mm × mm)	23 × 23	27 × 27	33 × 33

General Description

Similar to APEX 20K and APEX 20KE devices, APEX 20KC devices offer the MultiCore architecture, which combines the strengths of LUT-based and product-term-based devices with an enhanced memory structure. LUT-based logic provides optimized performance and efficiency for data-path, register-intensive, mathematical, or digital signal processing (DSP) designs. Product-term-based logic is optimized for complex combinatorial paths, such as complex state machines. LUT- and product-term-based logic combined with memory functions and a wide variety of MegaCore and AMPP functions make the APEX 20KC architecture uniquely suited for SOPC designs. Applications historically requiring a combination of LUT-, product-term-, and memory-based devices can now be integrated into one APEX 20KC device.

The counter mode uses two 3-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading, and another AND gate provides synchronous clearing. If the cascade function is used by an LE in counter mode, the synchronous clear or load overrides any signal carried on the cascade chain. The synchronous clear overrides the synchronous load. LEs in arithmetic mode can drive out registered and unregistered versions of the LUT output.

Clear & Preset Logic Control

Logic for the register's clear and preset signals is controlled by LAB-wide signals. The LE directly supports an asynchronous clear function. The Quartus II Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset or to emulate simultaneous preset and clear or asynchronous load. However, this technique uses three additional LEs per register. All emulation is performed automatically when the design is compiled. Registers that emulate simultaneous preset and load will enter an unknown state upon power-up or when the chip-wide reset is asserted.

In addition to the two clear and preset modes, APEX 20KC devices provide a chip-wide reset pin (DEV_CLRn) that resets all registers in the device. Use of this pin is controlled through an option in the Quartus II software that is set before compilation. The chip-wide reset overrides all other control signals. Registers using an asynchronous preset are preset when the chip-wide reset is asserted; this effect results from the inversion technique used to implement the asynchronous preset.

FastTrack Interconnect

In the APEX 20KC architecture, connections between LEs, ESBs, and I/O pins are provided by the FastTrack interconnect. The FastTrack interconnect is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack interconnect consists of row and column interconnect channels that span the entire device. The row interconnect routes signals throughout a row of MegaLAB structures; the column interconnect routes signals throughout a column of MegaLAB structures. When using the row and column interconnect, an LE, IOE, or ESB can drive any other LE, IOE, or ESB in a device. See Figure 9.

Figure 12. APEX 20KC FastRow Interconnect

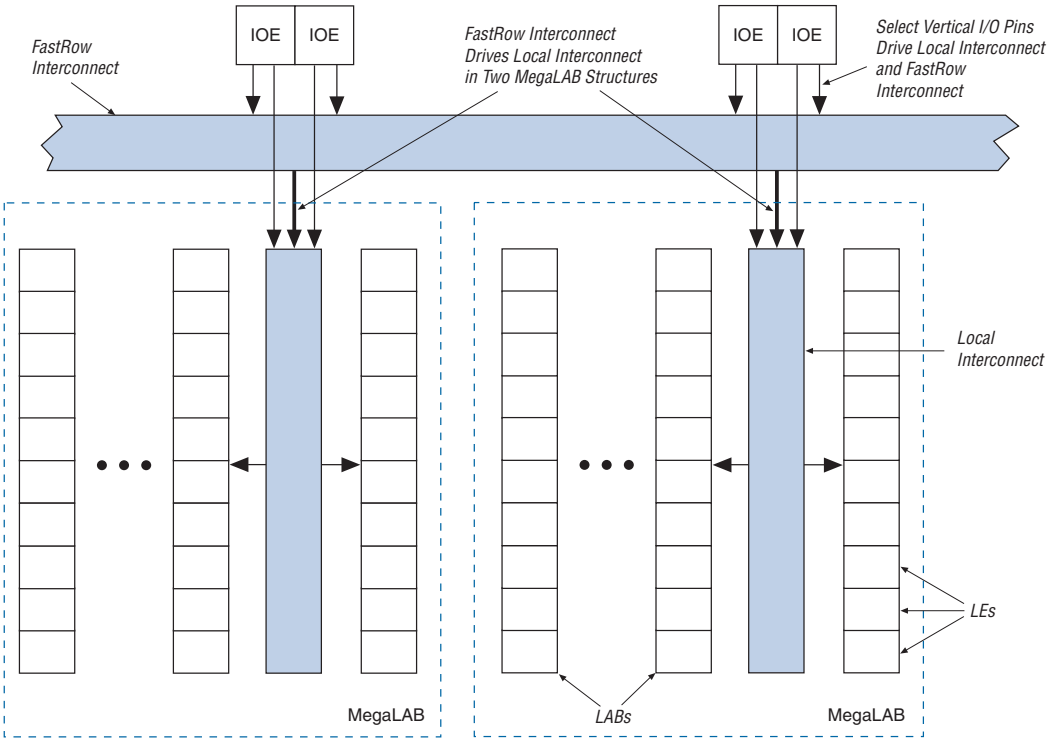
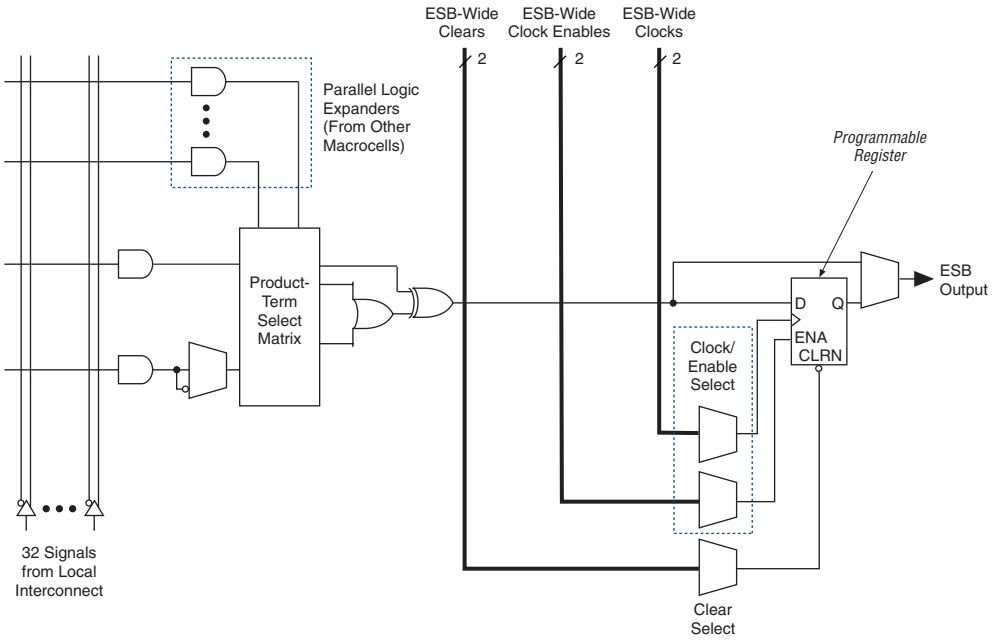


Table 8 summarizes how various elements of the APEX 20KC architecture drive each other.

Figure 14. APEX 20KC Macrocell

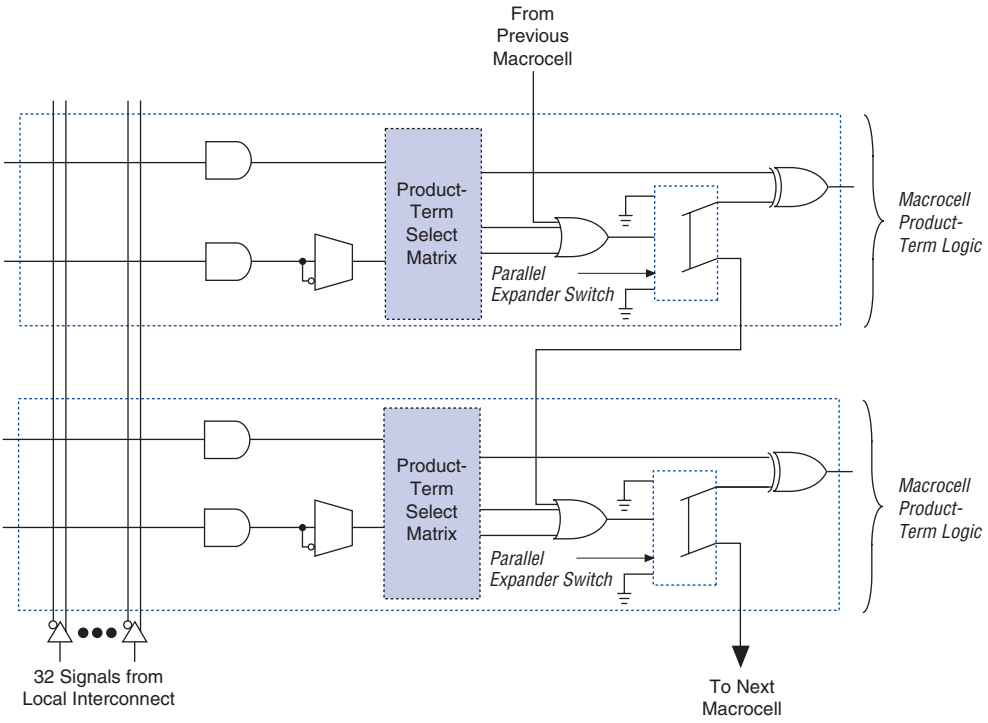


For registered functions, each macrocell register can be programmed individually to implement D, T, JK, or SR operation with programmable clock control. The register can be bypassed for combinatorial operation. During design entry, the designer specifies the desired register type; the Quartus II software then selects the most efficient register operation for each registered function to optimize resource utilization. The Quartus II software or other synthesis tools can also select the most efficient register operation automatically when synthesizing HDL designs.

Each programmable register can be clocked by one of two ESB-wide clocks. The ESB-wide clocks can be generated from device dedicated clock pins, global signals, or local interconnect. Each clock also has an associated clock enable, generated from the local interconnect. The clock and clock enable signals are related for a particular ESB; any macrocell using a clock also uses the associated clock enable.

If both the rising and falling edges of a clock are used in an ESB, both ESB-wide clock signals are used.

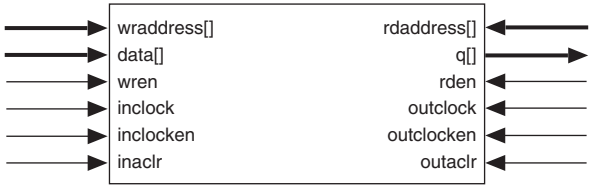
Figure 16. APEX 20KC Parallel Expanders



Embedded System Block

The ESB can implement various types of memory blocks, including dual-port RAM, ROM, FIFO, and CAM blocks. The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a dual-port mode, which supports simultaneous reads and writes at two different clock frequencies. Figure 17 shows the ESB block diagram.

Figure 17. ESB Block Diagram



ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the FastTrack or MegaLAB interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the FastTrack and MegaLAB interconnects. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

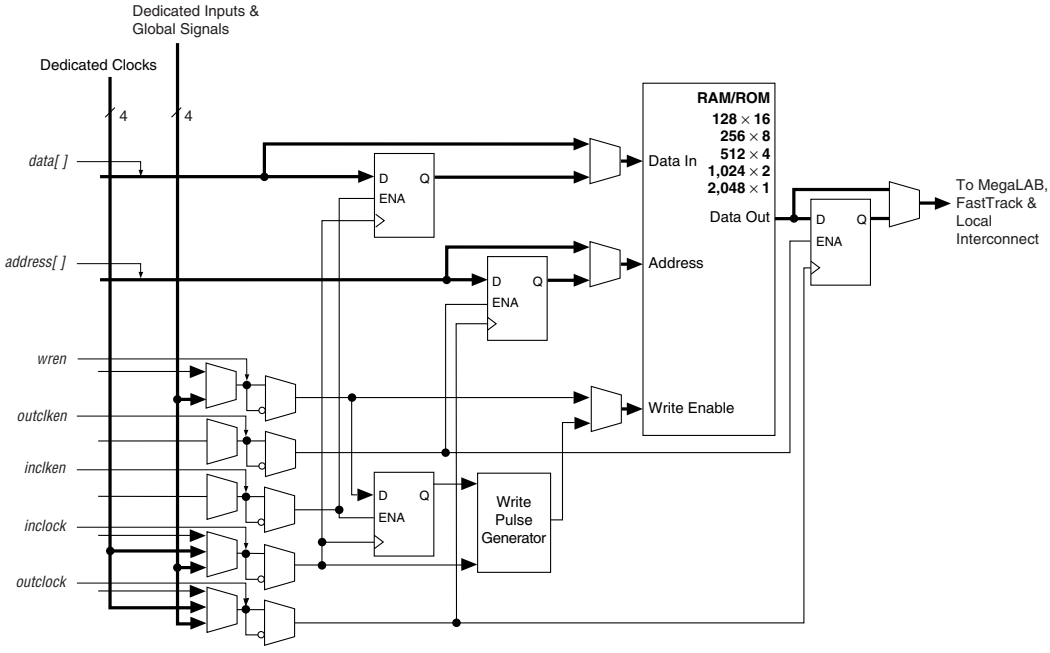
When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Single-Port Mode

The APEX 20KC ESB also supports a single-port mode, which is used when simultaneous reads and writes are not required. See Figure 22.

Figure 22. ESB in Single-Port Mode *Note (1)*



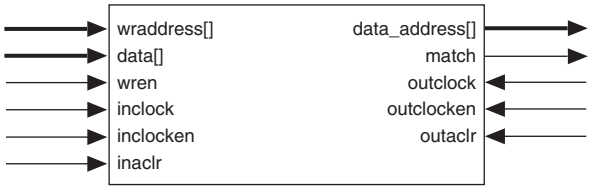
Note to Figure 22:

(1) All registers can be asynchronously cleared by ESB local interconnect signals, global signals, or the chip-wide reset.

Content-Addressable Memory

In APEX 20KC devices, the ESB can implement CAM. CAM can be thought of as the inverse of RAM. When read, RAM outputs the data for a given address. Conversely, CAM outputs an address for a given data word. For example, if the data `FA12` is stored in address `14`, the CAM outputs `14` when `FA12` is driven into it.

Figure 23. APEX 20KC CAM Block Diagram



CAM can be used in any application requiring high-speed searches, such as networking, communications, data compression, and cache management.

The APEX 20KC on-chip CAM provides faster system performance than traditional discrete CAM. Integrating CAM and logic into the APEX 20KC device eliminates off-chip and on-chip delays, improving system performance.

When in CAM mode, the ESB implements 32-word, 32-bit CAM. Wider or deeper CAM can be implemented by combining multiple CAMs with some ancillary logic implemented in LEs. The Quartus II software combines ESBs and LEs automatically to create larger CAMs.

CAM supports writing "don't care" bits into words of the memory. The "don't care" bit can be used as a mask for CAM comparisons; any bit set to "don't care" has no effect on matches.

The output of the CAM can be encoded or unencoded. When encoded, the ESB outputs an encoded address of the data's location. For instance, if the data is located in address `12`, the ESB output is `12`. When unencoded, the ESB uses its 16 outputs to show the location of the data over two clock cycles. In this case, if the data is located in address `12`, the 12th output line goes high. When using unencoded outputs, two clock cycles are required to read the output because a 16-bit output bus is used to show the status of 32 words.

The encoded output is better suited for designs that ensure duplicate data is not written into the CAM. If duplicate data is written into two locations, the CAM's output will be incorrect. If the CAM may contain duplicate data, the unencoded output is a better solution; CAM with unencoded outputs can distinguish multiple data locations.

CAM can be pre-loaded with data during configuration, or it can be written during system operation. In most cases, two clock cycles are required to write each word into CAM. When "don't care" bits are used, a third clock cycle is required.

The register in the APEX 20KC IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. This feature is useful for cases where the APEX 20KC device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Figure 25 shows how fast bidirectional I/O pins are implemented in APEX 20KC devices. This feature is useful for cases where the APEX 20KC device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Notes to Figure 25:
(1) This programmable delay has four settings: off and three levels of delay.
(2) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. Figure 26 shows how a row IOE connects to the interconnect.

Figure 26. Row IOE Connection to the Interconnect

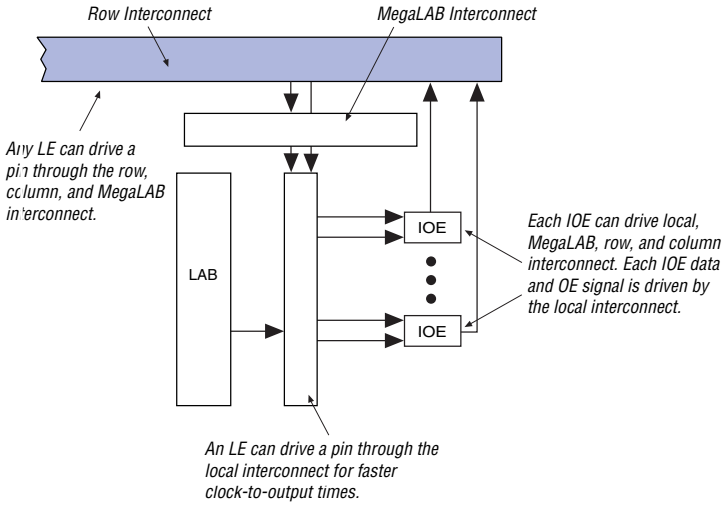
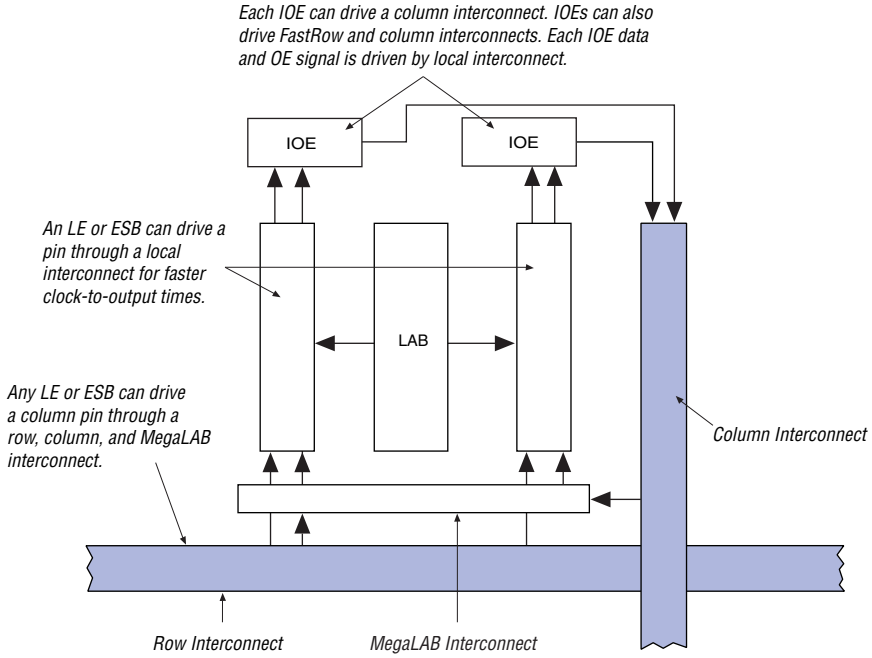


Figure 27 shows how a column IOE connects to the interconnect.

Figure 27. Column IOE Connection to the Interconnect



Dedicated Fast I/O Pins

APEX 20KC devices incorporate an enhancement to support bidirectional pins with high internal fan-out such as PCI control signals. These pins are called dedicated fast I/O pins (`FAST1`, `FAST2`, `FAST3`, and `FAST4`) and replace dedicated inputs. These pins can be used for fast clock, clear, or high fan-out logic signal distribution. They also can drive out. The dedicated fast I/O pin data output and tri-state control are driven by local interconnect from the adjacent MegaLAB for high speed.

Advanced I/O Standard Support

APEX 20KC IOEs support the following I/O standards: LVTTL, LVCMOS, 1.8-V I/O, 2.5-V I/O, 3.3-V PCI, PCI-X, 3.3-V AGP, LVDS, LVPECL, GTL+, CTT, HSTL Class I, SSTL-3 Class I and II, and SSTL-2 Class I and II.

For more information on I/O standards supported by APEX 20KC devices, see *Application Note 117 (Using Selectable I/O Standards in Altera Devices)*.

The APEX 20KC device contains eight I/O banks. In QFP packages, the banks are linked to form four I/O banks. The I/O banks directly support all standards except LVDS and LVPECL. All I/O banks can support LVDS and LVPECL at up to 156 Mbps per channel with the addition of external resistors. In addition, one block within a bank contains circuitry to support high-speed True-LVDS and LVPECL inputs, and another block within a bank supports high-speed True-LVDS and LVPECL outputs. The LVDS blocks support all of the I/O standards. Each I/O bank has its own VCCIO pins. A single device can support 1.8-V, 2.5-V, and 3.3-V interfaces; each bank can support a different standard independently. Each bank can also use a separate V_{REF} level so that each bank can support any of the terminated standards (such as SSTL-3) independently. Within a bank, any one of the terminated standards can be supported. EP20K400C and larger APEX 20KC devices support the LVDS interface for data pins (EP20K200C devices support LVDS clock pins, but not data pins). EP20K400C and EP20K600C devices support LVDS for data pins at up to 840 Mbps per channel. EP20K1000C devices support LVDS on 16 channels at up to 750 Mbps.

Each bank can support multiple standards with the same VCCIO for output pins. Each bank can support one voltage-referenced I/O standard, but it can support multiple I/O standards with the same VCCIO voltage level. For example, when VCCIO is 3.3 V, a bank can support LVTTL, LVCMOS, 3.3-V PCI, and SSTL-3 for inputs and outputs.

When the LVDS banks are not used for the LVDS I/O standard, they support all of the other I/O standards. Figure 28 shows the arrangement of the APEX 20KC I/O banks.

Clock Multiplication

The APEX 20KC ClockBoost circuit can multiply or divide clocks by a programmable number. The clock can be multiplied by $m/(n \times k)$, where m and k range from 2 to 160 and n ranges from 1 to 16. Clock multiplication and division can be used for time-domain multiplexing and other functions, which can reduce design LE requirements.

Clock Phase & Delay Adjustment

The APEX 20KC ClockShift feature allows the clock phase and delay to be adjusted. The clock phase can be adjusted by 90° steps. The clock delay can be adjusted to increase or decrease the clock delay by an arbitrary amount, up to one clock period.

LVDS Support

All APEX 20KC devices support differential LVDS buffers on the input and output clock signals that interface with external devices. This is controlled in the Quartus II software by assigning the clock pins with an LVDS I/O standard assignment.

Two high-speed PLLs are designed to support the LVDS interface. When using LVDS, the I/O clock runs at a slower rate than the data transfer rate. Thus, PLLs are used to multiply the I/O clock internally to capture the LVDS data. For example, an I/O clock may run at 105 MHz to support 840 Mbps LVDS data transfer. In this example, the PLL multiplies the incoming clock by eight to support the high-speed data transfer. You can use PLLs in EP20K400C and larger devices for high-speed LVDS interfacing.

Lock Signals

The APEX 20KC ClockLock circuitry supports individual `LOCK` signals. The `LOCK` signal drives high when the ClockLock circuit has locked onto the input clock. The `LOCK` signals are optional for each ClockLock circuit; when not used, they are I/O pins.

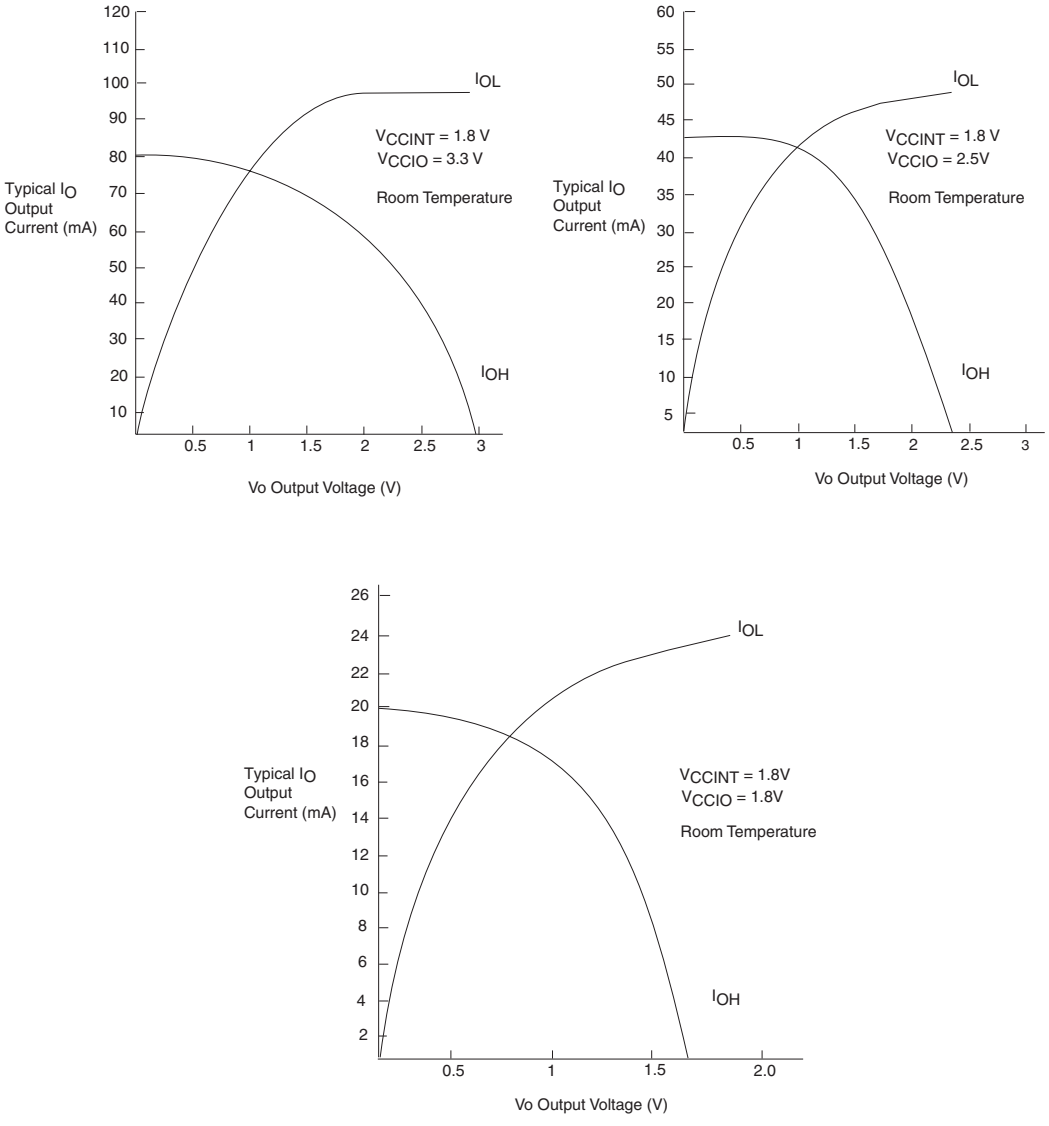
Table 26. 3.3-V PCI-X Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{IH}	High-level input voltage		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage		–0.5		0.35 × V_{CCIO}	V
V_{IPU}	Input pull-up voltage		0.7 × V_{CCIO}			V
I_{IL}	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10.0		10.0	µA
V_{OH}	High-level output voltage	I_{OUT} = –500 µA	0.9 × V_{CCIO}			V
V_{OL}	Low-level output voltage	I_{OUT} = 1,500 µA			0.1 × V_{CCIO}	V
L_{pin}	Pin Inductance				15.0	nH

Table 27. 3.3-V LVDS I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.135	3.3	3.465	V
V_{OD}	Differential output voltage	R_L = 100 Ω	250		650	mV
Δ V_{OD}	Change in V_{OD} between high and low	R_L = 100 Ω			50	mV
V_{OS}	Output offset voltage	R_L = 100 Ω	1.125	1.25	1.375	V
Δ V_{OS}	Change in V_{OS} between high and low	R_L = 100 Ω			50	mV
V_{TH}	Differential input threshold	V_{CM} = 1.2 V	–100		100	mV
V_{IN}	Receiver input voltage range		0.0		2.4	V
R_L	Receiver differential input resistor (external to APEX devices)		90	100	110	Ω

Figure 31. Output Drive Characteristics of APEX 20KC Devices *Note (1)*



Note to Figure 31:

(1) These are transient (AC) currents.

Figure 33. ESB Asynchronous Timing Waveforms

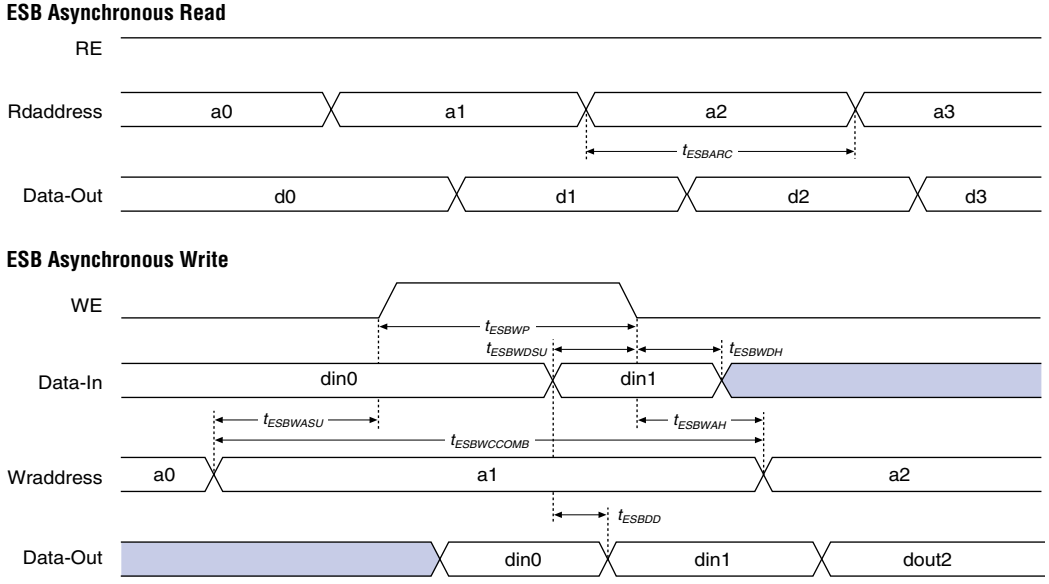


Table 39. APEX 20KC Minimum Pulse Width Timing Parameters	
Symbol	**Parameter**
t_{CH}	Minimum clock high time from clock pin
t_{CL}	Minimum clock low time from clock pin
t_{CLRP}	LE clear pulse width
t_{PREP}	LE preset pulse width
t_{ESBCH}	Clock high time
t_{ESBCL}	Clock low time
t_{ESBWP}	Write pulse width
t_{ESBRP}	Read pulse width

Tables 40 and 41 describe APEX 20KC external timing parameters. The timing values for these pin-to-pin delays are reported for all pins using the 3.3-V LVTTL I/O standard.

Table 40. APEX 20KC External Timing Parameters *Note (1)*		
Symbol	**Clock Parameter**	**Conditions**
t_{INSU}	Setup time with global clock at IOE register	
t_{INH}	Hold time with global clock at IOE register	
t_{OUTCO}	Clock-to-output delay with global clock at IOE output register	*(2)*
$t_{INSUPLL}$	Setup time with PLL clock at IOE input register	
t_{INHPLL}	Hold time with PLL clock at IOE input register	
$t_{OUTCOPLL}$	Clock-to-output delay with PLL clock at IOE output register	*(2)*

Table 49. EP20K200C External Bidirectional Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	1.38		1.78		1.99		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	3.79	2.00	4.31	2.00	4.70	ns
$t_{XZBIDIR}$		6.12		6.51		7.89	ns
$t_{ZXBIDIR}$		6.12		6.51		7.89	ns
$t_{INSUBIDIRPLL}$	2.82		3.47		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.36	0.50	2.62	-	-	ns
$t_{XZBIDIRPLL}$		4.69		4.82		-	ns
$t_{ZXBIDIRPLL}$		4.69		4.82		-	ns

Table 50. EP20K400C f_{MAX} LE Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.01		0.01		ns
t_{H}	0.10		0.10		0.10		ns
t_{CO}		0.27		0.30		0.32	ns
t_{LUT}		0.65		0.78		0.92	ns

Table 53. EP20K400C Minimum Pulse Width Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.33		1.66		2.00		ns
t_{CL}	1.33		1.66		2.00		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.33		1.66		2.00		ns
t_{ESBCL}	1.33		1.66		2.00		ns
t_{ESBWP}	1.05		1.28		1.44		ns
t_{ESBRP}	0.87		1.06		1.19		ns

Table 54. EP20K400C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.37		1.52		1.64		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.25	2.00	4.61	2.00	5.03	ns
$t_{INSUPLL}$	0.80		0.91		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.27	0.50	2.55	-	-	ns